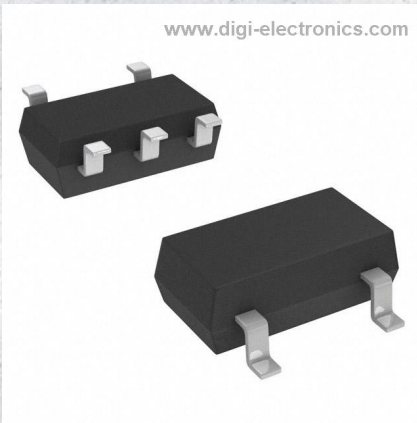


# XN0A31100L Datasheet



|                              |   |
|------------------------------|---|
| DiGi Electronics Part Number | XN0A31100L-DG   |
| Manufacturer                 | <a href="#">Panasonic Electronic Components</a>   |
| Manufacturer Product Number  | XN0A31100L  |
| Description                  | TRANS NPN/PNP PREBIAS 0.3W MINI5  |
| Detailed Description         | Pre-Biased Bipolar Transistor (BJT) 1 NPN, 1 PNP - P re-Biased (Dual) 50V 100mA 150MHz, 80MHz 300m W Surface Mount Mini5-G1 |



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## Purchase and inquiry

Manufacturer Product Number:

XN0A31100L

Series:

-

Transistor Type:

1 NPN, 1 PNP - Pre-Biased (Dual)

Voltage - Collector Emitter Breakdown (Max):

50V

Resistor - Emitter Base (R2):

10kOhms

Vce Saturation (Max) @ Ib, Ic:

250mV @ 300µA, 10mA

Frequency - Transition:

150MHz, 80MHz

Mounting Type:

Surface Mount

Supplier Device Package:

Mini5-G1

Manufacturer:

Panasonic Electronic Components

Product Status:

Obsolete

Current - Collector (Ic) (Max):

100mA

Resistor - Base (R1):

10kOhms

DC Current Gain (hFE) (Min) @ Ic, Vce:

35 @ 5mA, 10V

Current - Collector Cutoff (Max):

500nA

Power - Max:

300mW

Package / Case:

SC-74A, SOT-753

Base Product Number:

XN0A31

## Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

HTSUS:

8541.21.0095

ECCN:

EAR99

# XN0A311 (XN1A311)

Silicon NPN epitaxial planar type (Tr1)  
 Silicon PNP epitaxial planar type (Tr2)

For switching

## ■ Features

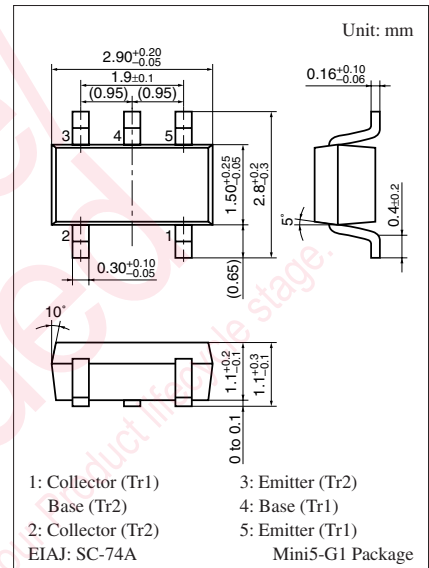
- Two elements incorporated into one package  
 (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

## ■ Basic Part Number

- UNR2211 (UN2211) + UNR2111 (UN2111)

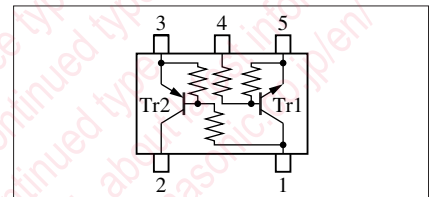
## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

|         | Parameter                                | Symbol    | Rating      | Unit             |
|---------|--|-----------|-------------|------------------|
| Tr1     | Collector-base voltage<br>(Emitter open) | $V_{CB0}$ | 50          | V                |
|         | Collector-emitter voltage<br>(Base open) | $V_{CEO}$ | 50          | V                |
|         | Collector current                        | $I_C$     | 100         | mA               |
| Tr2     | Collector-base voltage<br>(Emitter open) | $V_{CB0}$ | -50         | V                |
|         | Collector-emitter voltage<br>(Base open) | $V_{CEO}$ | -50         | V                |
|         | Collector current                        | $I_C$     | -100        | mA               |
| Overall | Total power dissipation                  | $P_T$     | 300         | mW               |
|         | Junction temperature                     | $T_j$     | 150         | $^\circ\text{C}$ |
|         | Storage temperature                      | $T_{stg}$ | -55 to +150 | $^\circ\text{C}$ |



Marking Symbol: FN

Internal Connection



Note) The part number in the parenthesis shows conventional part number.

■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr1

| Parameter                                    | Symbol        | Conditions   | Min  | Typ | Max  | Unit             |
|--|---------------|--|------|-----|------|------------------|
| Collector-base voltage (Emitter open)        | $V_{CBO}$     | $I_C = 10 \mu\text{A}, I_E = 0$                                      | 50   |     |      | V                |
| Collector-emitter voltage (Base open)        | $V_{CEO}$     | $I_C = 2 \text{ mA}, I_B = 0$  | 50   |     |      | V                |
| Collector-base cutoff current (Emitter open) | $I_{CBO}$     | $V_{CB} = 50 \text{ V}, I_E = 0$                                     |      |     | 0.1  | $\mu\text{A}$    |
| Collector-emitter cutoff current (Base open) | $I_{CEO}$     | $V_{CE} = 50 \text{ V}, I_B = 0$                                     |      |     | 0.5  | $\mu\text{A}$    |
| Emitter-base cutoff current (Collector open) | $I_{EBO}$     | $V_{EB} = 6 \text{ V}, I_C = 0$                                      |      |     | 0.5  | mA               |
| Forward current transfer ratio               | $h_{FE}$      | $V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$                          | 35   |     |      | —                |
| Collector-emitter saturation voltage         | $V_{CE(sat)}$ | $I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$                          |      |     | 0.25 | V                |
| Output voltage high-level                    | $V_{OH}$      | $V_{CC} = 5 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | 4.9  |     |      | V                |
| Output voltage low-level                     | $V_{OL}$      | $V_{CC} = 5 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1 \text{ k}\Omega$ |      |     | 0.2  | V                |
| Input resistance                             | $R_1$         |  | -30% | 10  | +30% | $\text{k}\Omega$ |
| Resistance ratio                             | $R_1 / R_2$   |  | 0.8  | 1.0 | 1.2  | —                |
| Transition frequency                         | $f_T$         | $V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$    |      | 150 |      | MHz              |

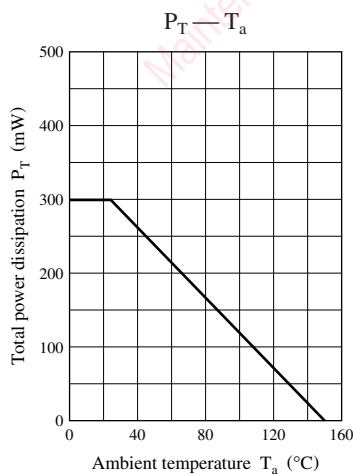
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• Tr2

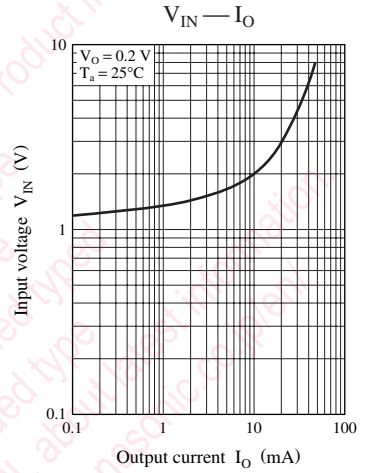
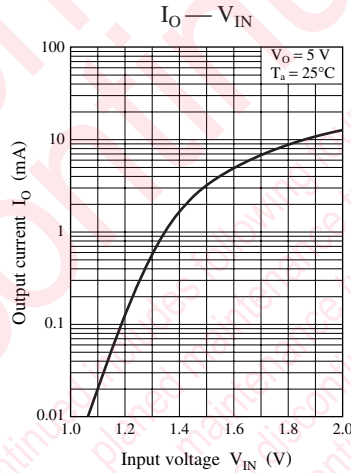
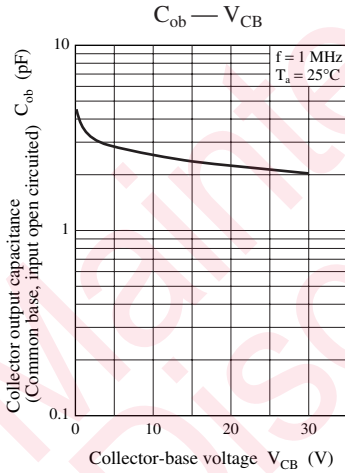
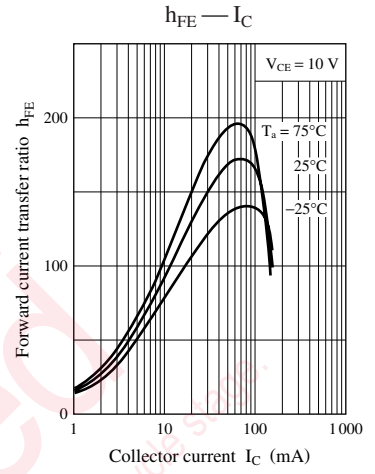
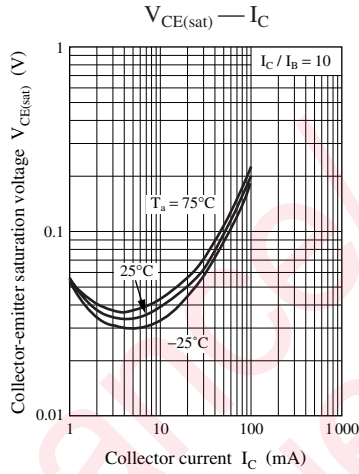
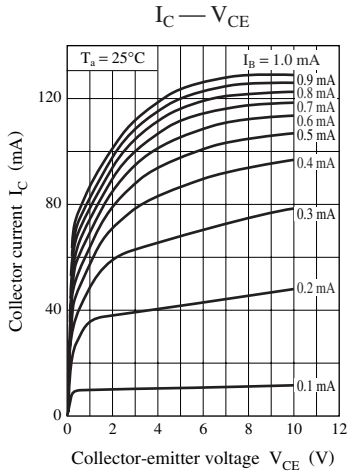
| Parameter                                    | Symbol        | Conditions   | Min  | Typ | Max   | Unit             |
|--|---------------|--|------|-----|-------|------------------|
| Collector-base voltage (Emitter open)        | $V_{CBO}$     | $I_C = -10 \mu\text{A}, I_E = 0$                                       | -50  |     |       | V                |
| Collector-emitter voltage (Base open)        | $V_{CEO}$     | $I_C = -2 \text{ mA}, I_B = 0$   | -50  |     |       | V                |
| Collector-base cutoff current (Emitter open) | $I_{CBO}$     | $V_{CB} = -50 \text{ V}, I_E = 0$                                      |      |     | -0.1  | $\mu\text{A}$    |
| Collector-emitter cutoff current (Base open) | $I_{CEO}$     | $V_{CE} = -50 \text{ V}, I_B = 0$                                      |      |     | -0.5  | $\mu\text{A}$    |
| Emitter-base cutoff current (Collector open) | $I_{EBO}$     | $V_{EB} = -6 \text{ V}, I_C = 0$                                       |      |     | -0.5  | mA               |
| Forward current transfer ratio               | $h_{FE}$      | $V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$                          | 35   |     |       | —                |
| Collector-emitter saturation voltage         | $V_{CE(sat)}$ | $I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$                          |      |     | -0.25 | V                |
| Output voltage high-level                    | $V_{OH}$      | $V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$ | -4.9 |     |       | V                |
| Output voltage low-level                     | $V_{OL}$      | $V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$ |      |     | -0.2  | V                |
| Input resistance                             | $R_1$         |  | -30% | 10  | +30%  | $\text{k}\Omega$ |
| Resistance ratio                             | $R_1 / R_2$   |  | 0.8  | 1.0 | 1.2   | —                |
| Transition frequency                         | $f_T$         | $V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$      |      | 80  |       | MHz              |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

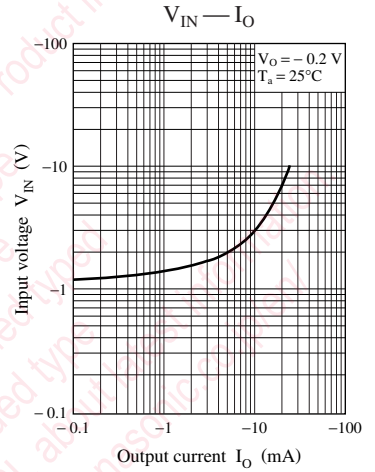
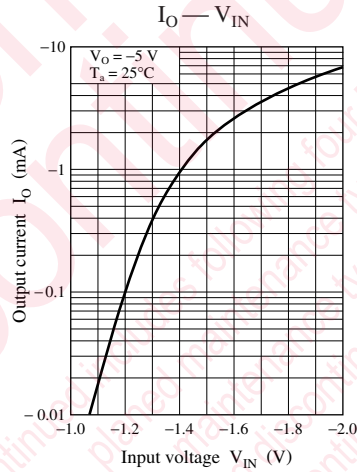
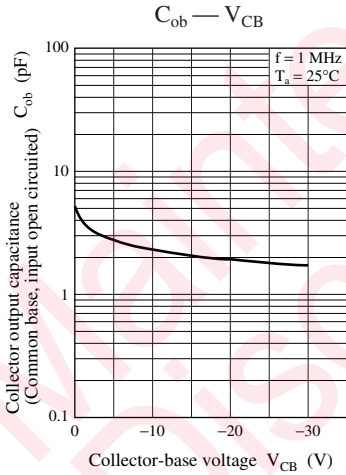
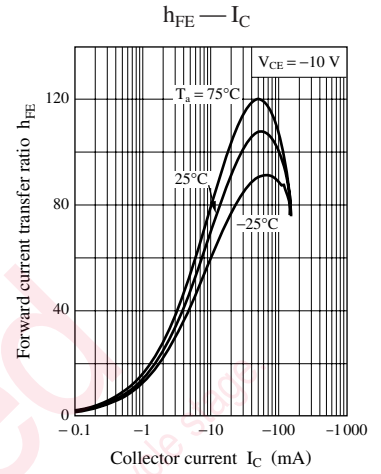
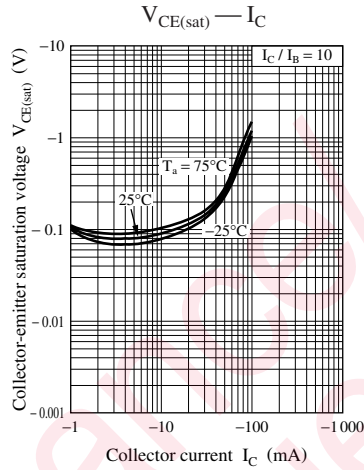
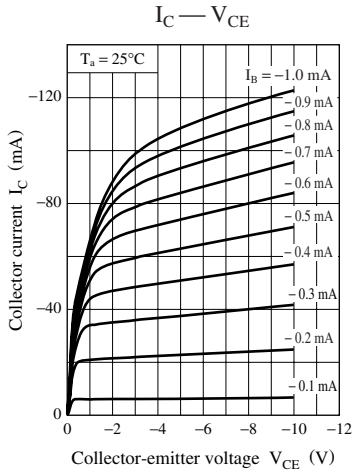
Common characteristics chart



Characteristics charts of Tr1



Characteristics charts of Tr2



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